

B1
Cmt

1) said observation part includes a first MOS transistor having:

i) a source/drain region including a first impurity region of a first conductivity type, that is connected with said first end of said wire and that is formed within a second impurity region of a second conductivity type; and

ii) a gate electrode that is electrically insulated from a gate electrode of said second MOS transistor; and

2) said pn junction includes said first and second impurity regions.

B2

6. (Twice Amended) The semiconductor device according to claim 1, wherein:

said portion measured is said gate electrode of said second MOS transistor.

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11. (Twice Amended) The semiconductor device according to claim 1, wherein:

a) said first conductivity type is an n type and said second conductivity type is a p type;

b) said observation part further includes:

1) a second pn junction having a p-type third impurity region connected with said wire; and an n-type fourth impurity region; and

c) a first fixed potential is applied to said second impurity region and a second fixed potential higher than said first fixed potential is applied to said fourth impurity region.

REMARKS

Favorable reconsideration of the above-identified patent application in light of the foregoing amendment and the following remarks is respectfully requested.

STATUS. Claims 1, 6-7, and 11 remain active in the application. Claims 1, 6, and 11 have been amended by way of the present amendment.

THE JULY 2, 2002 OFFICE ACTION. In the Office Action dated July 3, 2002, the restriction requirement was made final; FIG. 11 was objected to as not being labeled "Prior Art";